

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK369

For Low Noise Audio Amplifier Applications

Unit: mm

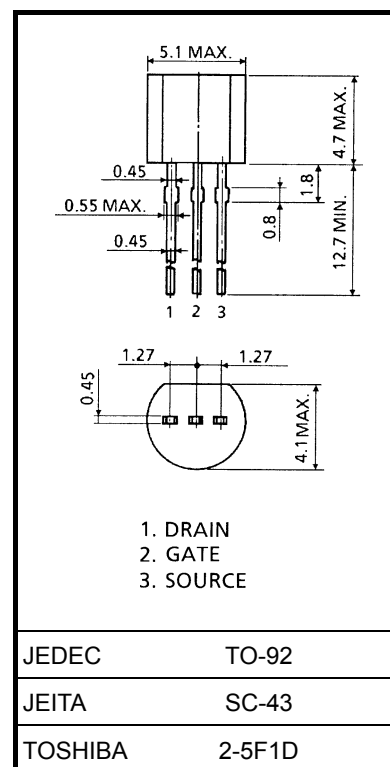
- Suitable for use as first stage for equalizer and MC head amplifiers.
- High $|Y_{fs}|$: $|Y_{fs}| = 40 \text{ mS (typ.)}$ ($V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $I_{DSS} = 5 \text{ mA}$)
- High breakdown voltage: $V_{GDS} = -40 \text{ V (min)}$
- Super low noise: $NF = 1.0\text{dB (typ.)}$
($V_{DS} = 10 \text{ V}$, $I_D = 5 \text{ mA}$, $f = 1 \text{ kHz}$, $R_G = 100 \Omega$)
- High input impedance: $I_{GSS} = -1 \text{ nA (max)}$ ($V_{GS} = -30 \text{ V}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	-40	V
Gate current	I_G	10	mA
Drain power dissipation	P_D	400	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.21 g (typ.)

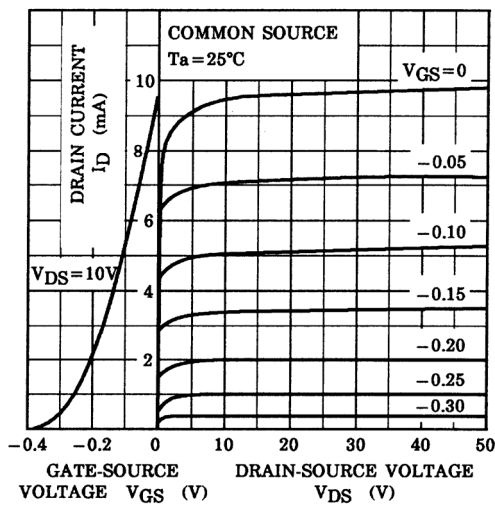
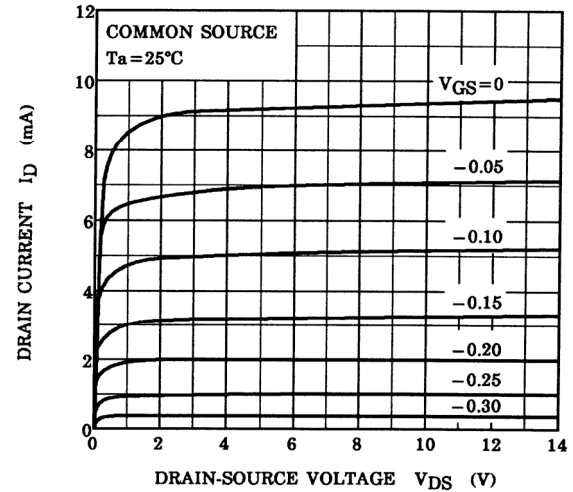
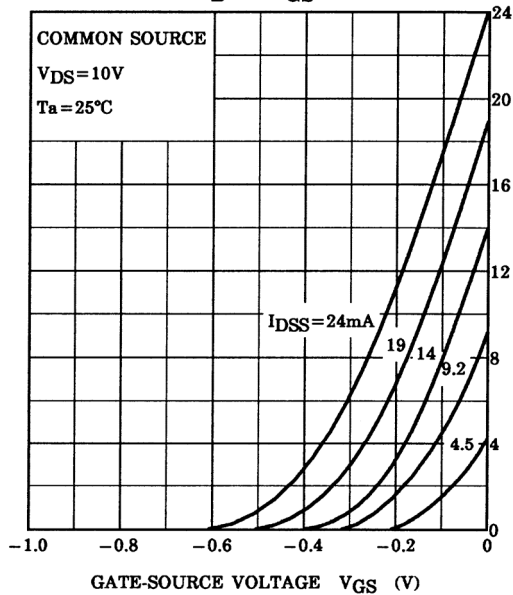
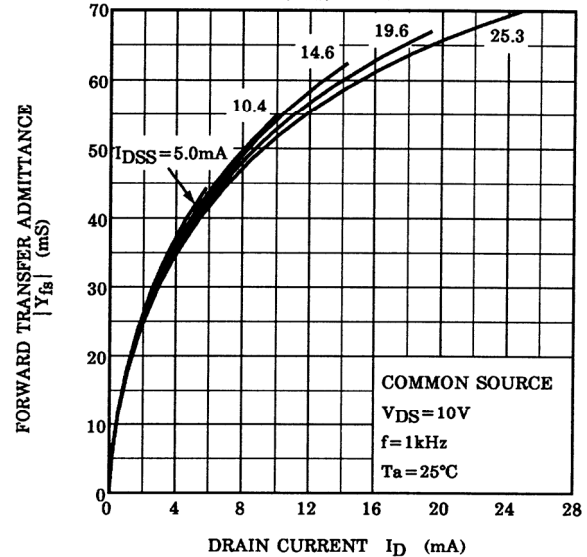
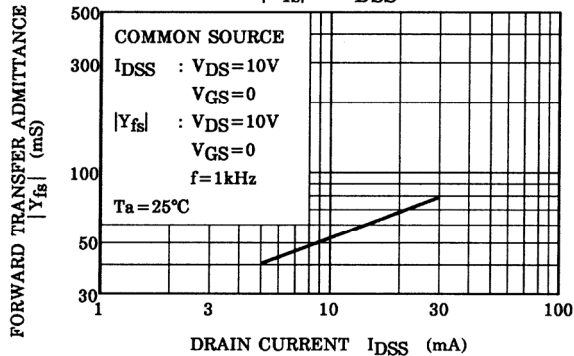
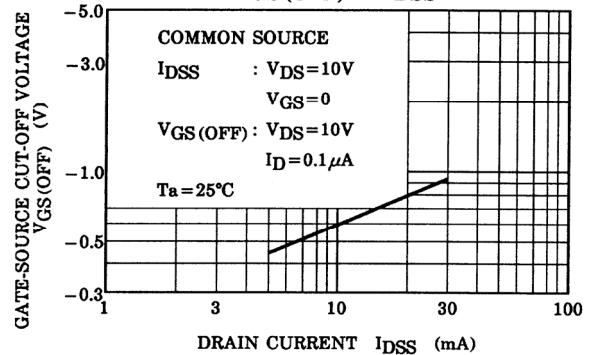
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

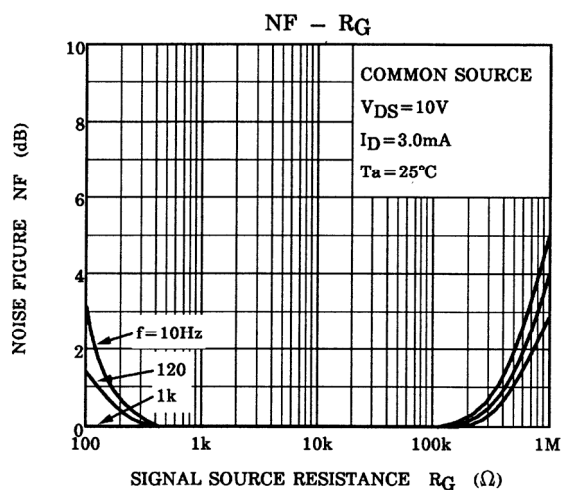
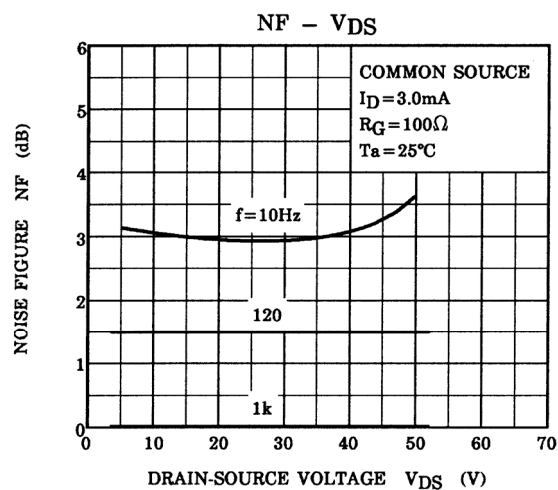
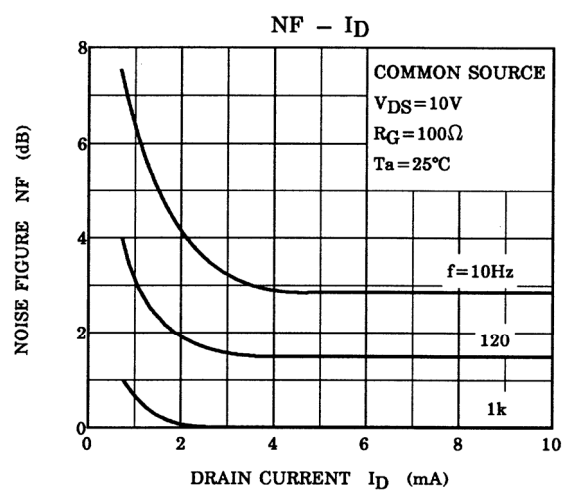
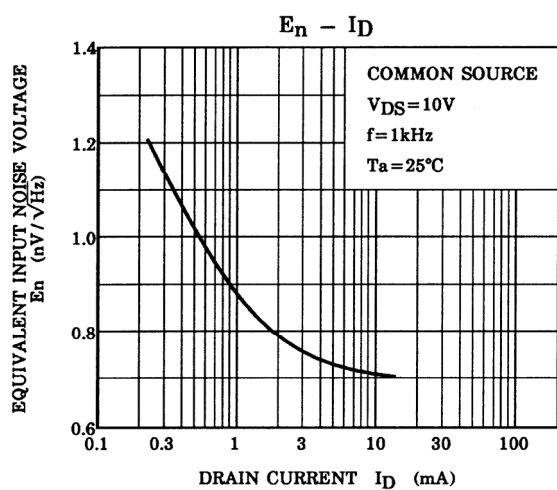
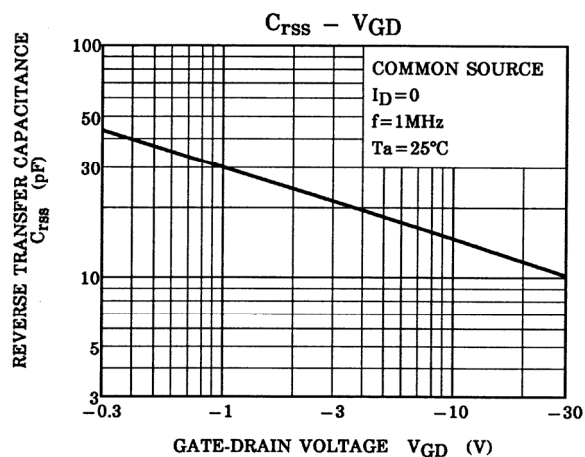
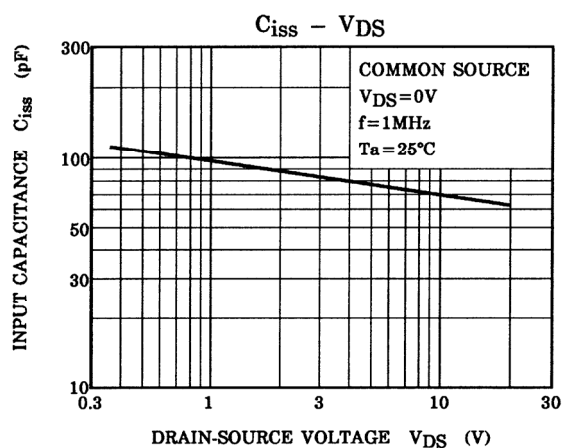
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	I_{GSS}	$V_{GS} = -30 \text{ V}$, $V_{DS} = 0$	—	—	-1.0	nA
Gate-drain breakdown voltage	$V_{(BR)GDS}$	$V_{DS} = 0$, $I_G = -100 \mu\text{A}$	-40	—	—	V
Drain current	I_{DSS} (Note 1)	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$	5.0	—	30	mA
Gate-source cut-off voltage	$V_{GS(OFF)}$	$V_{DS} = 10 \text{ V}$, $I_D = 0.1 \mu\text{A}$	-0.3	—	-1.2	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ kHz}$, ($I_{DSS} = 5 \text{ mA}$)	25	40	—	mS
Input capacitance	C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$	—	75	—	pF
Reverse transfer capacitance	C_{rss}	$V_{GD} = -10 \text{ V}$, $I_D = 0$, $f = 1 \text{ MHz}$	—	15	—	pF
Noise figure (Note 2)	NF (1)	$V_{DS} = 10 \text{ V}$, $R_G = 100 \Omega$, $I_D = 5 \text{ mA}$, $f = 100 \text{ Hz}$	—	5	10	dB
	NF (2)	$V_{DS} = 10 \text{ V}$, $R_G = 100 \Omega$, $I_D = 5 \text{ mA}$, $f = 1 \text{ kHz}$	—	1	2	

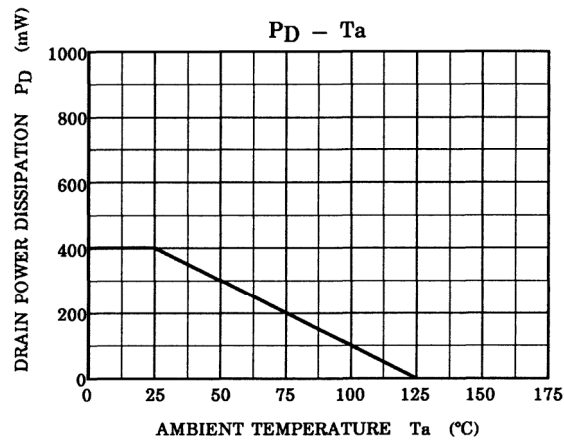
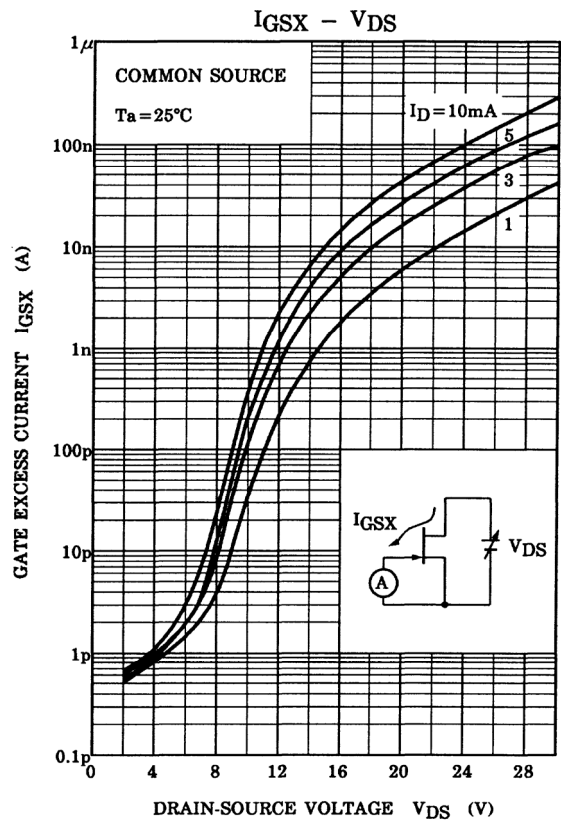
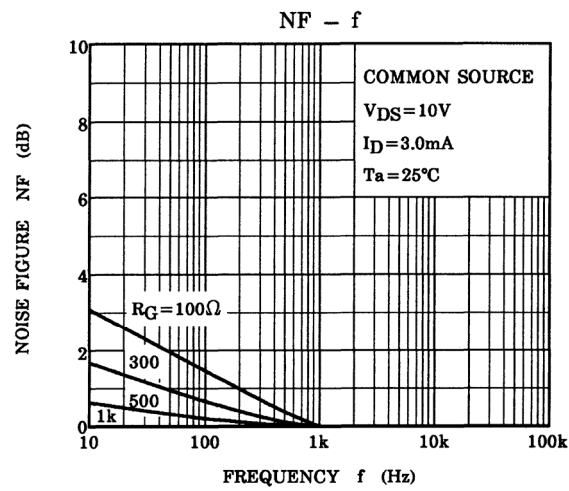
Note 1: I_{DSS} classification GR: 5.0~10.0 mA, BL: 8.0~16.0 mA, V: 14.0~30.0 mA

Note 2: Use this in the low voltage region ($V_{DS} < 15 \text{ V}$) for low noise applications.

STATIC CHARACTERISTICS

 $I_D - V_{DS}$ (LOW VOLTAGE REGION) $I_D - V_{GS}$  $|Y_{fs}| - I_D$  $|Y_{fs}| - I_{DSS}$  $V_{GS(OFF)} - I_{DSS}$ 





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20070701-EN GENERAL

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